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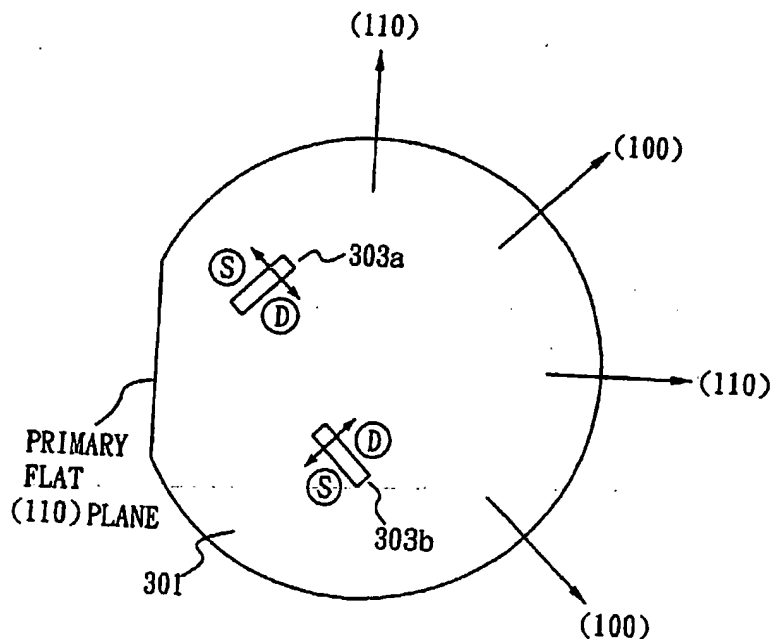
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(54) Title: CMOS FABRICATION PROCESS UTILIZING SPECIAL TRANSISTOR ORIENTATION



(57) Abstract: Complementary metal oxide semiconductor transistors are formed on a silicon substrate. The substrate has a {100} crystallographic orientation. The transistors are formed on the substrate so that current flows in the channels of the transistors are parallel to the <100> direction. Additionally, longitudinal tensile stress is applied to the channels.

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INTERNATIONAL SEARCH REPORT

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A. CLASSIFICATION OF SUBJECT MATTER
IPC 7 H01L21/8238 H01L27/092

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)
IPC 7 H01L

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practical, search terms used)

EPO-Internal, PAJ, WPI Data, INSPEC, IBM-TDB

C. DOCUMENTS CONSIDERED TO BE RELEVANT

| Category * | Citation of document, with indication, where appropriate, of the relevant passages | Relevant to claim No. |
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| -/- | | |

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☒ Patent family members are listed in annex.

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| Y | | <p>3-5,7-9, 12-15</p> |
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